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FQT13N06L

N-Channel QFET[®] MOSFET

60 V, 2.8 A, 110 mΩ

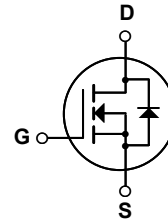
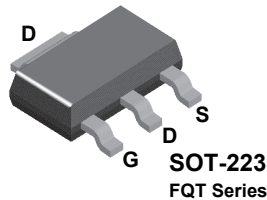
FQT13N06L — N-Channel QFET[®] MOSFET

General Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor[®]'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 2.8 A, 60 V, $R_{DS(on)} = 110 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 1.4 \text{ A}$
- Low Gate Charge (Typ. 4.8 nC)
- Low C_{rss} (Typ. 17 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQT13N06L	Unit
V_{DSS}	Drain-Source Voltage	60	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 70^\circ\text{C}$)	2.8	A
		2.24	A
I_{DM}	Drain Current - Pulsed (Note 1)	11.2	A
V_{GSS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	85	mJ
I_{AR}	Avalanche Current (Note 1)	2.8	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	0.21	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	2.1	W
		0.017	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	60	$^\circ\text{C}/\text{W}$

* When mounted on the minimum pad size recommended(PCB mount).

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.05	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 48\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0	--	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 1.4\text{ A}$	--	0.088	0.11	Ω
		$V_{GS} = 5\text{ V}, I_D = 1.4\text{ A}$	--	0.110	0.14	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 25\text{ V}, I_D = 1.4\text{ A}$ (Note 4)	--	4.1	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	270	350	pF
C_{oss}	Output Capacitance		--	95	125	pF
C_{rss}	Reverse Transfer Capacitance		--	17	23	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}, I_D = 6.8\text{ A},$ $R_G = 25\ \Omega$	--	8	25	ns	
t_r	Turn-On Rise Time		--	90	190	ns	
$t_{d(off)}$	Turn-Off Delay Time		--	20	50	ns	
t_f	Turn-Off Fall Time		(Note 4, 5)	--	40	90	ns
Q_g	Total Gate Charge		$V_{DS} = 48\text{ V}, I_D = 13.6\text{ A},$ $V_{GS} = 5\text{ V}$	--	4.8	6.4	nC
Q_{gs}	Gate-Source Charge	(Note 4, 5)	--	1.6	--	nC	
Q_{gd}	Gate-Drain Charge		--	2.7	--	nC	

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	2.8	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	11.2	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.8\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 13.6\text{ A},$	--	45	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	45	--	nC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. $L = 12.6\text{ mH}, I_{AS} = 2.8\text{ A}, V_{DD} = 25\text{ V}, R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 13.6\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Pulse test : pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$.
5. Essentially independent of operating temperature.

Typical Characteristics

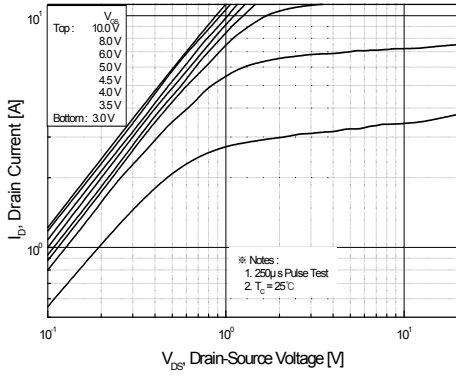


Figure 1. On-Region Characteristics

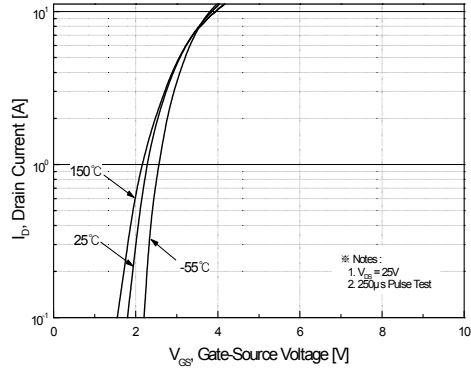


Figure 2. Transfer Characteristics

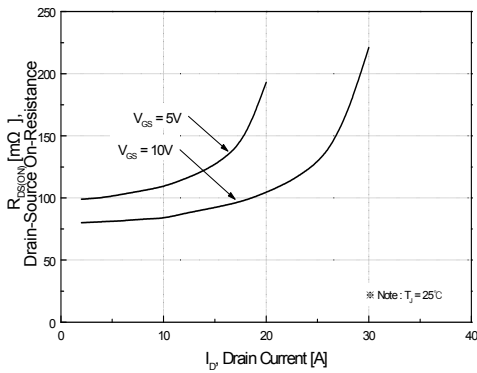


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

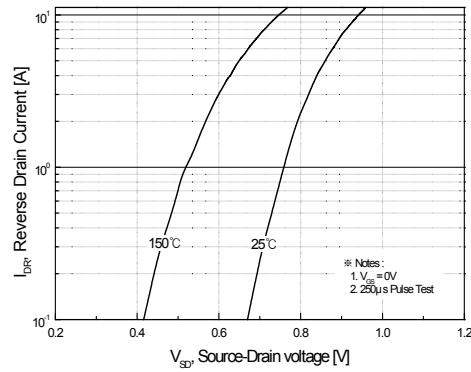


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

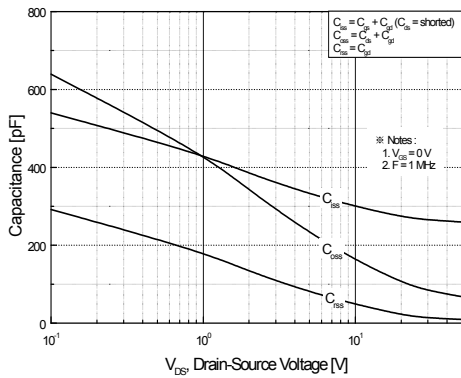


Figure 5. Capacitance Characteristics

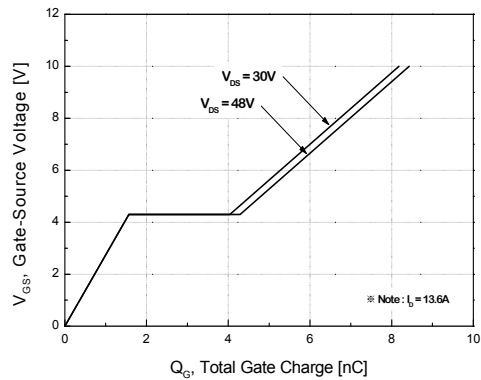


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

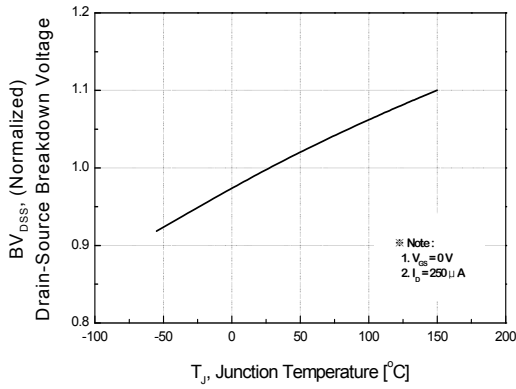


Figure 7. Breakdown Voltage Variation vs Temperature

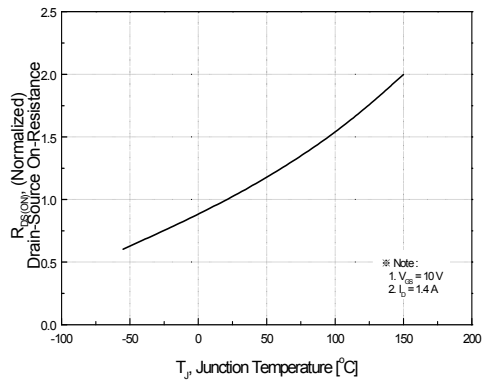


Figure 8. On-Resistance Variation vs Temperature

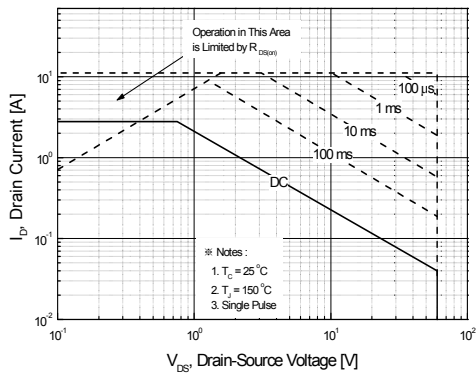


Figure 9. Maximum Safe Operating Area

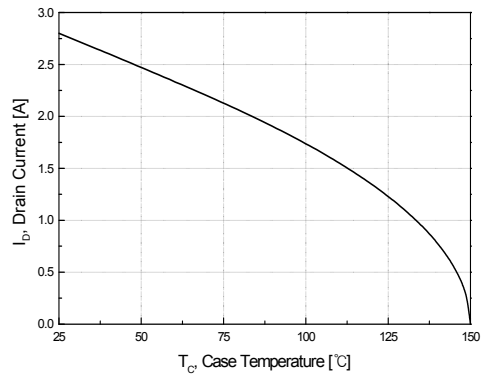


Figure 10. Maximum Drain Current vs Case Temperature

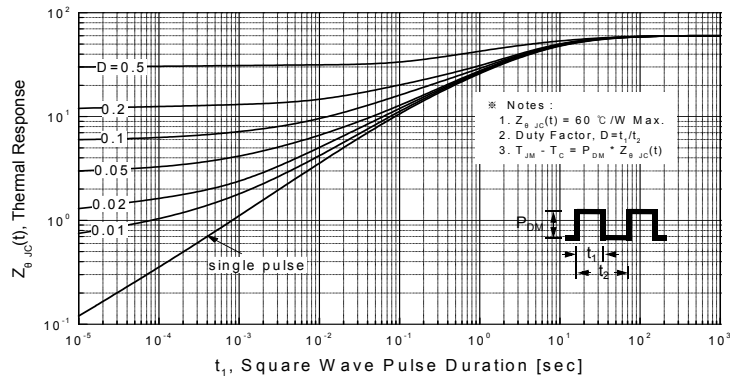


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

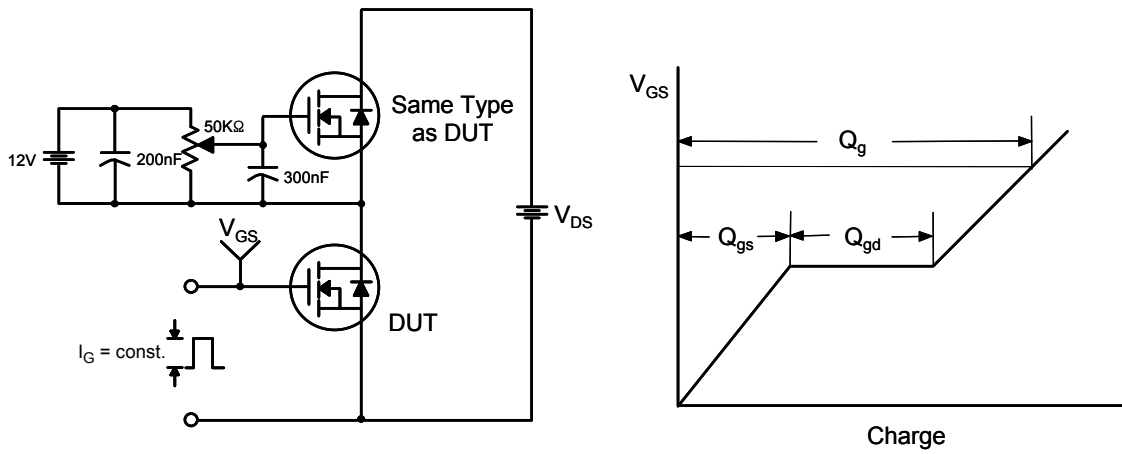


Figure 13. Resistive Switching Test Circuit & Waveforms

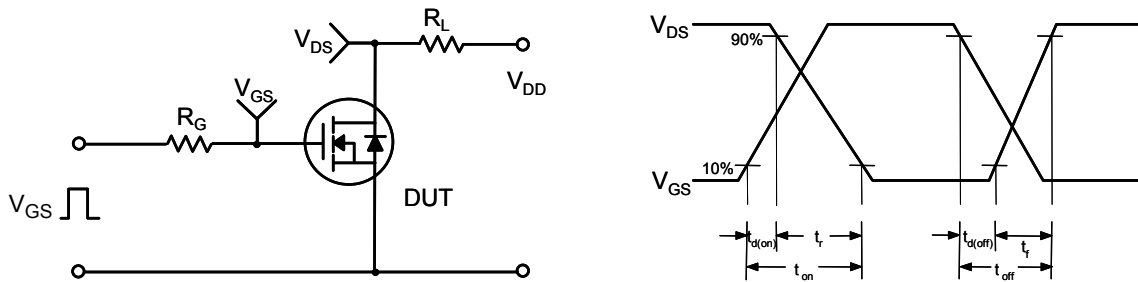


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

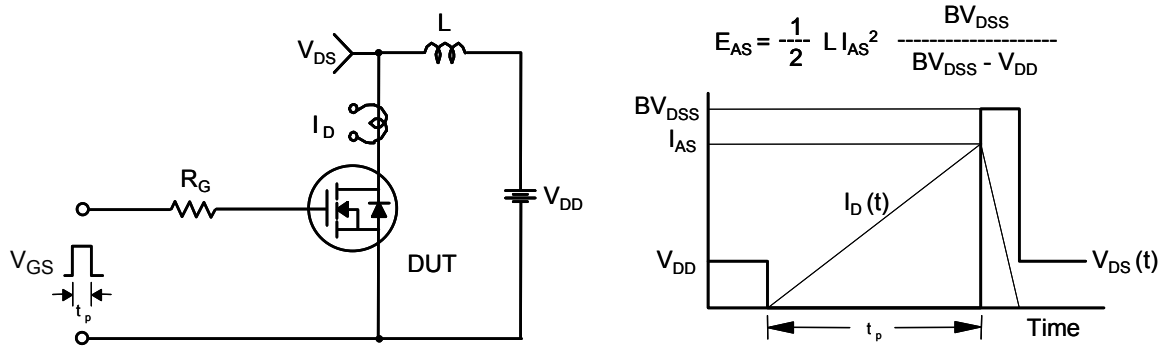
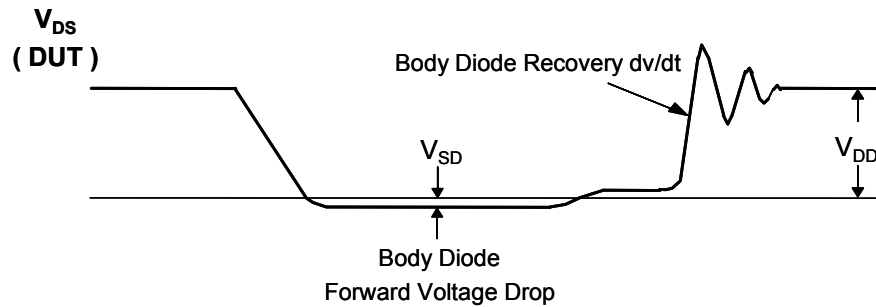
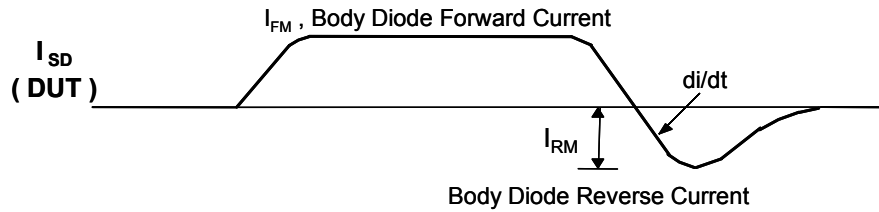
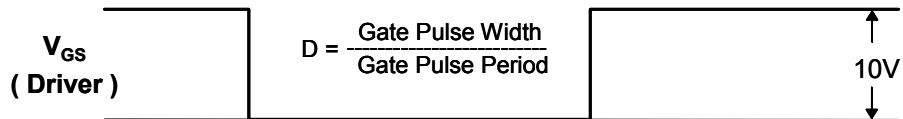
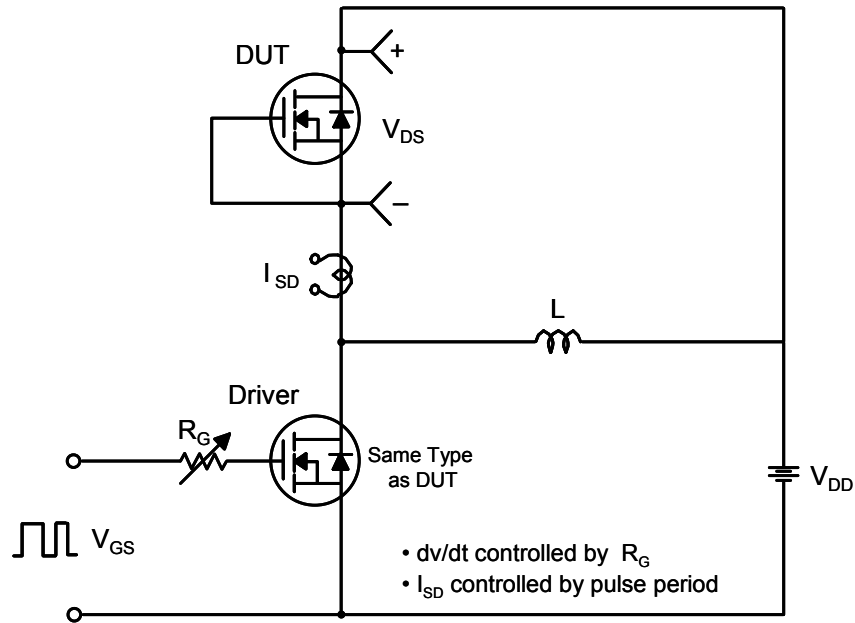
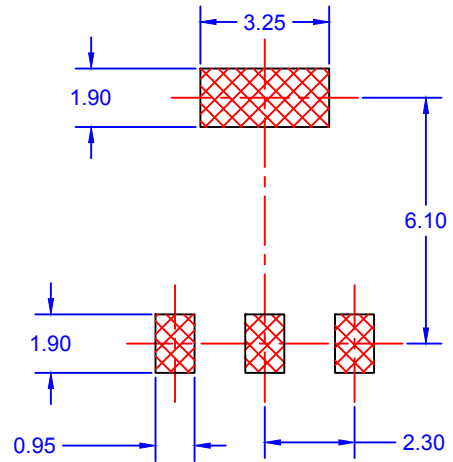
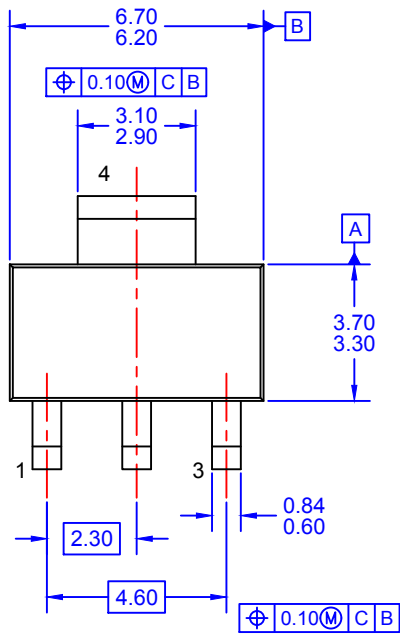
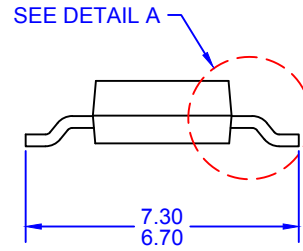
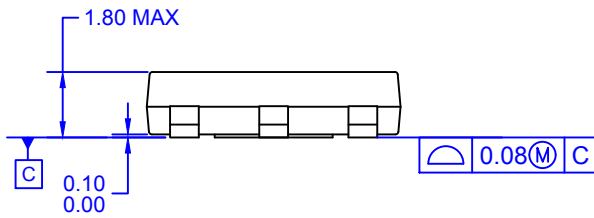


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

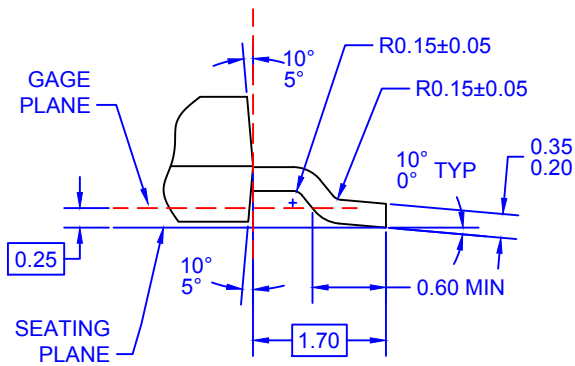




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 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
 D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 E) LANDPATTERN NAME: SOT230P700X180-4BN
 F) DRAWING FILENAME: MKT-MA04AREV3



DETAIL A
 SCALE: 2:1



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